

IRLR120TRRPBF

IRLR120TRRPBF Information



For Reference Only

Part Number IRLR120TRRPBF Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 7.7A DPAK

Package TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com E-mail: salesdept@heisener.com

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IRLR120TRRPBF Specifications

Manufacturer Part Number IRLR120TRRPBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 7.7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 5V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 12nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 490pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 2.5W (Ta), 42W (Tc) Rds On (Max) @ Id, Vgs 270 mOhm @ 4.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 Report errors?		
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Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 7.7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 5V Vgs(th) (Max) @ Id 2V @ 250μA Gate Charge (Qg) (Max) @ Vgs 12nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 490pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 2.5W (Ta), 42W (Tc) Rds On (Max) @ Id, Vgs 270 mOhm @ 4.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer	Vishay Siliconix
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Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C7.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 5VInput Capacitance (Ciss) (Max) @ Vds490pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)2.5W (Ta), 42W (Tc)Rds On (Max) @ Id, Vgs270 mOhm @ 4.6A, 5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C7.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 5VInput Capacitance (Ciss) (Max) @ Vds490pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)2.5W (Ta), 42W (Tc)Rds On (Max) @ Id, Vgs270 mOhm @ 4.6A, 5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C7.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 5VInput Capacitance (Ciss) (Max) @ Vds490pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)2.5W (Ta), 42W (Tc)Rds On (Max) @ Id, Vgs270 mOhm @ 4.6A, 5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	-
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C7.7A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 5VInput Capacitance (Ciss) (Max) @ Vds490pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)2.5W (Ta), 42W (Tc)Rds On (Max) @ Id, Vgs270 mOhm @ 4.6A, 5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surplier Device Package Package / Case 7.7A (Tc) 849.50 2V @ 250μA 490pF @ 25V 25V (Ta), 42W (Tc) 270 mOhm @ 4.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 5VInput Capacitance (Ciss) (Max) @ Vds490pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)2.5W (Ta), 42W (Tc)Rds On (Max) @ Id, Vgs270 mOhm @ 4.6A, 5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +10V FET Feature - Power Dissipation (Max) As On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	7.7A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 490pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 270 mOhm @ 4.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	4V, 5V
Input Capacitance (Ciss) (Max) @ Vds 490pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 270 mOhm @ 4.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max) ± 10 VFET Feature-Power Dissipation (Max) 2.5 W (Ta), 42 W (Tc)Rds On (Max) @ Id, Vgs 270 mOhm @ 4.6 A, 5 VOperating Temperature -55° C $\sim 150^{\circ}$ C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	12nC @ 5V
FET Feature - Power Dissipation (Max) 2.5W (Ta), 42W (Tc) Rds On (Max) @ Id, Vgs 270 mOhm @ 4.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	490pF @ 25V
Power Dissipation (Max) 2.5W (Ta), 42W (Tc) 270 mOhm @ 4.6A, 5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±10V
Rds On (Max) @ Id, Vgs270 mOhm @ 4.6A, 5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	2.5W (Ta), 42W (Tc)
Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	270 mOhm @ 4.6A, 5V
Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	D-Pak
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

IRLR120TRRPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRLR120TRRPBF Payment Methods



















IRLR120TRRPBF Shipping Methods













If you have any question about IRLR120TRRPBF, please do not hesitate to contact us!

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